

ABSTRACT OF THE DISCLOSURE

An amorphous-silicon thin film transistor and a shift resister shift resister having the amorphous-silicon TFT include a first conductive region, a second conductive region and a third conductive region. The first conductive region is formed on a first plane spaced apart from a substrate by a first distance. The second conductive region is formed on a second plane spaced apart from the substrate by a second distance. The second conductive region includes a body conductive region and two hand conductive regions elongated from both ends of the body conductive region to form an U-shape. The third conductive region is formed on the second plane. The third conductive region includes an elongated portion. The elongated portion is disposed between the two hand conductive regions of the second conductive region. The amorphous-silicon TFT and the shift resister having the amorphous TFT reduce a parasitic capacitance between the gate electrode and drain electrode.

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